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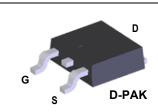
FQD7P06 P-Channel QFET[®] MOSFET - 60 V, - 5.4 A, 450 mΩ

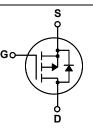
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor[®]'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 5.4 A, 60 V, $R_{DS(on)}$ = 450 m Ω (Max.) @ V_{GS} = 10 V, I_D = 2.7 A
- Low Gate Charge (Typ. 6.3 nC)
- Low Crss (Typ. 25 pF)
- 100% Avalanche Tested





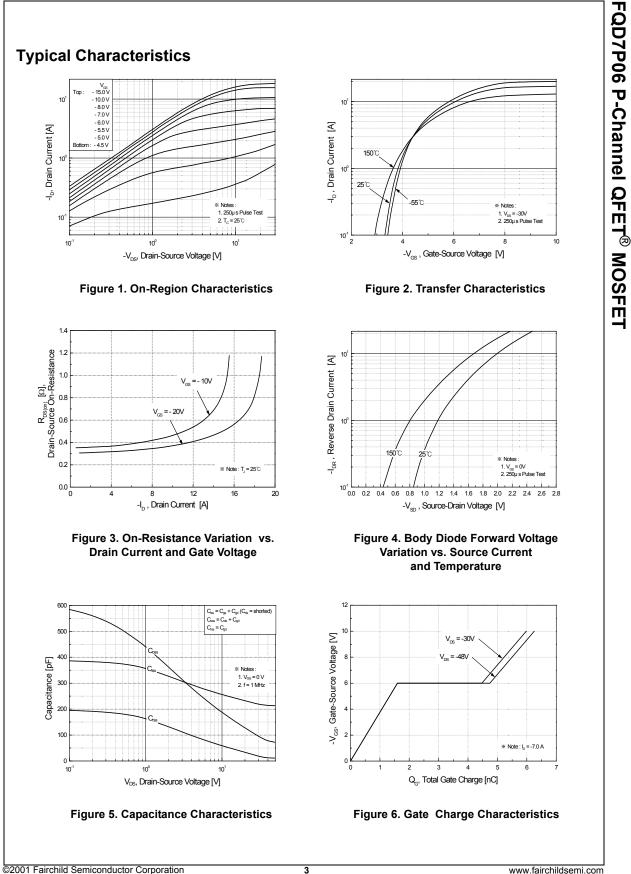
Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			FQD7P06	Unit	
V _{DSS}	Drain-Source Voltage		-60	V		
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		°C)	-5.4	А	
	- Continuous (T _C = 100°C		0°C)	-3.42	А	
I _{DM}	Drain Current	- Pulsed	(Note 1)	-21.6	А	
V _{GSS}	Gate-Source Voltage			± 25	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	90	mJ	
I _{AR}	Avalanche Current		(Note 1)	-5.4	Α	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	2.8	mJ	
dv/dt	Peak Diode Re	covery dv/dt	(Note 3)	-7.0	V/ns	
P _D	Power Dissipation (T _A = 25°C) *			2.5	W	
	Power Dissipation (T _C = 25°C)			28	W	
	- Derate above 25°C			0.22	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C		
ΤL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds			300	°C	

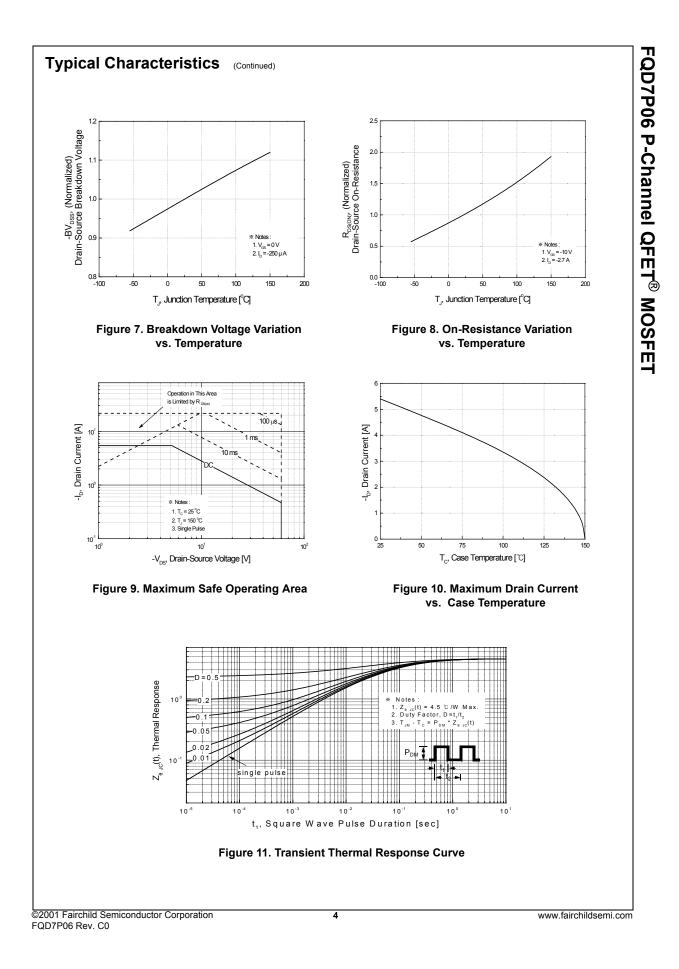
Thermal Characteristics

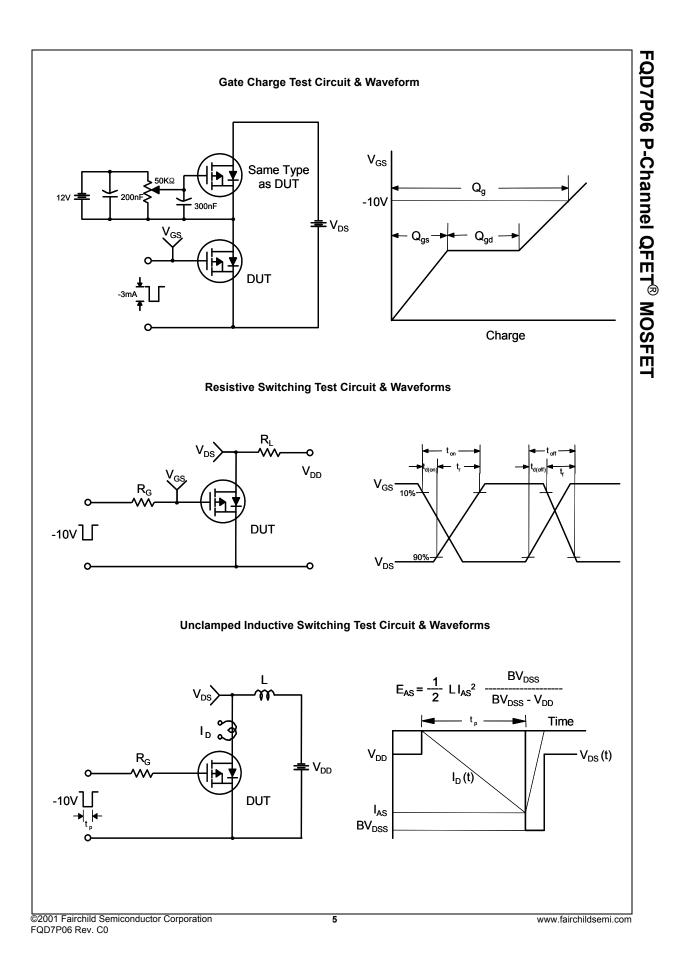
Symbol	Parameter	FQD7P06	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	4.5	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient *	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W

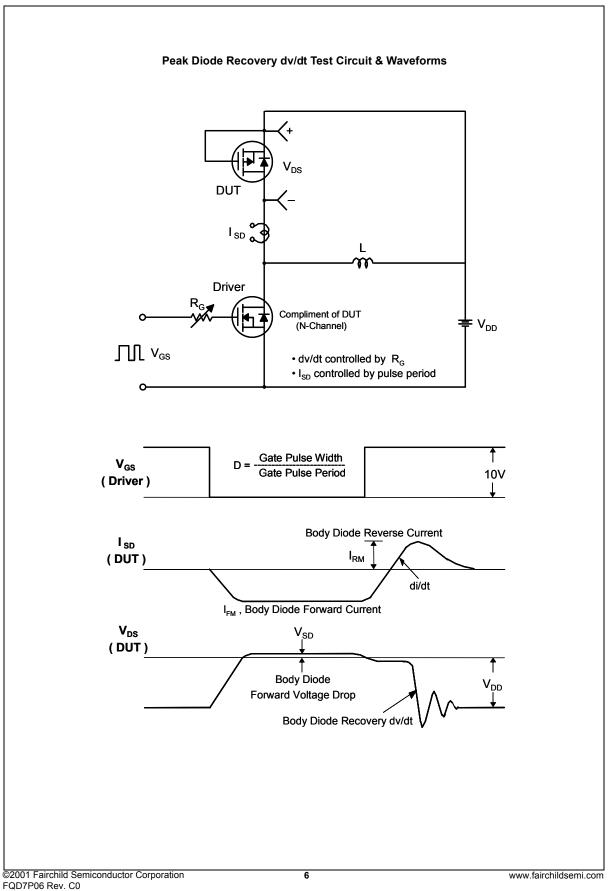
	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Ch₂	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA	-60			V
ΔBV _{DSS}	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to 25°C		-0.07		V/°C
DSS		V _{DS} = -60 V, V _{GS} = 0 V			-1	μA
000	Zero Gate Voltage Drain Current	$V_{DS} = -48 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$			-10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -25 V, V_{DS} = 0 V$			-100	nA
GSSR	Gate-Body Leakage Current, Reverse	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
On Cha	racteristics		1	L		
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -2.7 A		0.36	0.451	Ω
9 _{FS}	Forward Transconductance	V _{DS} = -30 V, I _D = -2.7 A		3.8		S
Dynam i C _{iss}	ic Characteristics			225	295	pF
	input oupdoitance	V _{DS} = -25 V, V _{GS} = 0 V,				•
	Output Capacitance			110	145	n –
rss	Output Capacitance Reverse Transfer Capacitance ng Characteristics	f = 1.0 MHz		110 25	145 32	pF pF
C _{oss} C _{rss} Switchi	Reverse Transfer Capacitance ng Characteristics			25	32	pF
C _{oss} C _{rss} Switchi	Reverse Transfer Capacitance	V _{DD} = -30 V, I _D = -3.5 A,				•
C _{oss} C _{rss} Switchi d(on)	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time			25 7	32 25	pF ns
C _{oss} C _{rss} Switchi d(on) fr d(off)	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time	V _{DD} = -30 V, I _D = -3.5 A,		25 7 50	32 25 110	pF ns ns
C _{oss} C _{rss} Switchi t ^d (on) tr t ^d (off) tf	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time	V_{DD} = -30 V, I _D = -3.5 A, R _G = 25 Ω (Note 4)	 	25 7 50 7.5	32 25 110 25	pF ns ns ns
C _{oss} C _{rss} Switchi td(on) tr td(off) tf Qg	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time	V_{DD} = -30 V, I _D = -3.5 A, R _G = 25 Ω	 	25 7 50 7.5 25	32 25 110 25 60	pF ns ns ns ns
C _{oss} C _{rss} Switchi d(on) d(off) d(off) d g Qg Qgs	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A},$ $R_{G} = 25 \Omega$ (Note 4) $V_{DS} = -48 \text{ V}, \text{ I}_{D} = -7.0 \text{ A},$		25 7 50 7.5 25 6.3	32 25 110 25 60 8.2	pF ns ns ns ns nC
C_{oss} C_{rss} Switchi $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g Q_{gs} Q_{gd} Drain-S	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics and	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A},$ $R_{G} = 25 \Omega$ (Note 4) $V_{DS} = -48 \text{ V}, \text{ I}_{D} = -7.0 \text{ A},$ $V_{GS} = -10 \text{ V}$ (Note 4) Note 4)	 	25 7 50 7.5 25 6.3 1.6	32 25 110 25 60 8.2 	pF ns ns ns nc nC
C_{oss} C_{rss} Switchi d(on) d(off) d(off) d_{gs} Q_{gs} Q_{gd} Drain-S	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics and Maximum Continuous Drain-Source Diode	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A},$ $R_{G} = 25 \Omega$ (Note 4) $V_{DS} = -48 \text{ V}, \text{ I}_{D} = -7.0 \text{ A},$ $V_{GS} = -10 \text{ V}$ (Note 4) (Note 4) (Note 4) (Note 4) (Note 4)	 	25 7 50 7.5 25 6.3 1.6	32 25 110 25 60 8.2 	pF ns ns ns nC nC nC
C _{oss} C _{rss} Switchi td(on) tr Qg Qgs Qgg Qgd Drain-S sM	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics and Maximum Continuous Drain-Source Diode F	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A},$ $R_{G} = 25 \Omega$ (Note 4) $V_{DS} = -48 \text{ V}, \text{ I}_{D} = -7.0 \text{ A},$ $V_{GS} = -10 \text{ V}$ (Note 4) nd Maximum Ratings ode Forward Current Forward Current	 	25 7 50 7.5 25 6.3 1.6	32 25 110 25 60 8.2 	pF ns ns ns nC nC nC
C _{oss} C _{rss} Switchi td(on) tr dd(off) tf Qg Qgs Qgd Drain-S Is SM VSD	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics and Maximum Continuous Drain-Source Diode F Drain-Source Diode Forward Voltage	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A}, \\ \text{R}_{G} = 25 \Omega $ (Note 4) $V_{DS} = -48 \text{ V}, \text{ I}_{D} = -7.0 \text{ A}, \\ \text{V}_{GS} = -10 \text{ V} $ (Note 4) (25 7 50 7.5 25 6.3 1.6 3.1	32 25 110 25 60 8.2 	pF ns ns ns nC nC nC
C _{oss} C _{rss} Switchi d(on) f d(off) f Qg Qgs Qgs Qgd Drain-S s SM	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics and Maximum Continuous Drain-Source Diode F	$V_{DD} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A},$ $R_{G} = 25 \Omega$ (Note 4) $V_{DS} = -48 \text{ V}, \text{ I}_{D} = -7.0 \text{ A},$ $V_{GS} = -10 \text{ V}$ (Note 4) nd Maximum Ratings ode Forward Current Forward Current	 	25 7 50 7.5 25 6.3 1.6 3.1	32 25 110 25 60 8.2 	pF ns ns ns nC nC nC



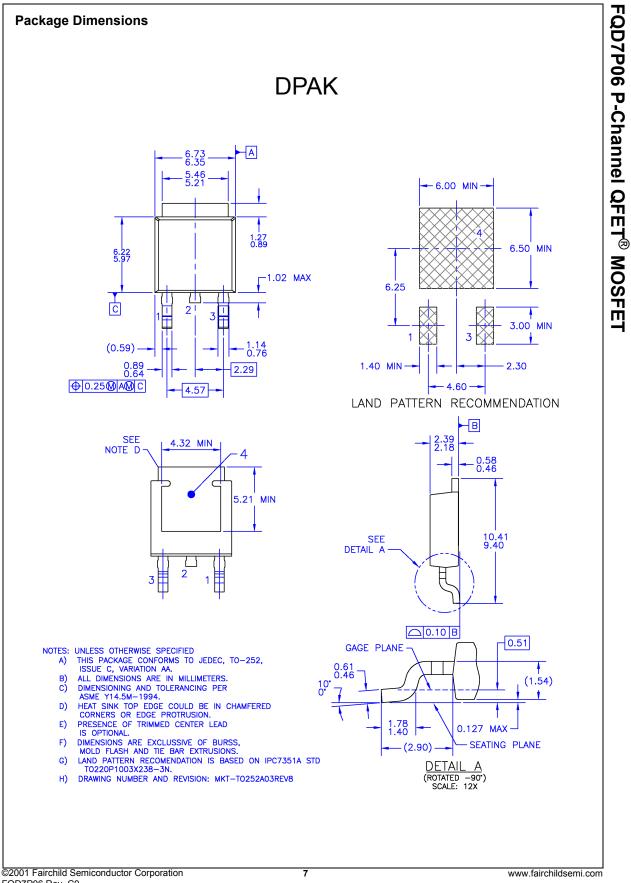
FQD7P06 Rev. C0







FQD7P06 P-Channel QFET® MOSFET





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